

BYT03-400

FAST RECOVERY RECTIFIER DIODE

MAJOR PRODUCTS CHARACTERISTICS

| I _{F(AV)} | 3 A |
|----------------------|-------|
| V _{RRM} | 400 V |
| t _{rr} | 25 ns |
| V _F (max) | 1.4 V |

FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING

DESCRIPTION

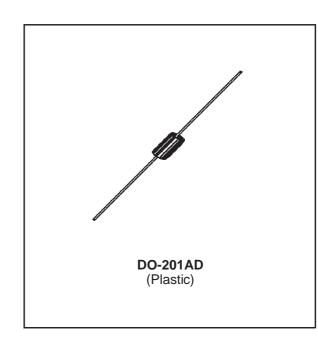
Free wheeling diode in converters and motor control circuits.

Rectifiers in S.M.P.S.

ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | Value | Unit | |
|---------------------|--|---|------|---|
| Vrrm | Repetitive peak reverse voltage | | 400 | V |
| V _{RSM} | Non repetitive peak reverse voltage | | 400 | V |
| IFRM | Repetive peak forward current | 60 | А | |
| I _{F (AV)} | Average forward current* | $\begin{array}{c} T_{a}=65^{\circ}C\\ \delta=0.5 \end{array}$ | 3 | A |
| IFSM | Surge non repetitive forward current | 60 | A | |
| Р | Power dissipation * | 4.2 | W | |
| T _{stg} | Storage temperature range | - 40 to + 150 | °C | |
| Tj | Maximum operating junction temperature | + 150 | | |

* On infinite heatsink with 10mm lead lengh.



BYT03-400

THERMAL RESISTANCES

| Symbol | Parameter | Value | Unit |
|-------------|-------------------|-------|------|
| Rth (j - a) | Junction-ambient* | 20 | °C/W |

* On infinite heatsink with 10mm lead lengh.

STATIC ELECTRICAL CHARACTERISTICS

| Synbol | Tes | Min. | Тур. | Max. | Unit | |
|----------------|-----------------------|---------------------|------|------|------|----|
| I _R | T _j = 25C | $V_{R} = V_{RRM}$ | | | 20 | μΑ |
| | T _j = 100C | | | | 0.5 | mA |
| VF | T _j = 25C | I _F = 3A | | | 1.5 | V |
| | T _j = 100C | | | | 1.4 | |

RECOVERY CHARACTERISTICS

| Symbol | | Min. | Тур. | Max. | Unit | |
|--------|---|---|------|------|------|----|
| trr | T _j = 25C IF = 1A diF/dt = - 15A/µs VR = 30V | | | | 55 | ns |
| | | $I_F = 0.5A$ $I_R = 1 A$ $I_{rr} = 0.25A$ | | | 25 | |

TURN-OFF SWITCHING CHARACTERISTICS - Without series inductance

| Symbol | Test Conditions | | | | Тур. | Max. | Unit |
|------------------|--------------------------------|------------------------|---|--|------|------|------|
| t _{IRM} | di _F /dt = - 50A/µs | $V_{CC} = 200 V$ | I _F = 3A T _i = 100°C | | 35 | 50 | ns |
| I _{RM} | di⊧/dt = -50A/µs | L _p ≤0.05µH | ij = 100°C | | 1.5 | 2 | А |

To evaluate the conduction losse use the following equations : $V_F = 1.1 + 0.050 I_F$ $P = 1.1 \times I_{F(AV)} + 0.050 I_F^{2}(_{RMS})$

Fig. 1: Maximum average power dissipation versus average forward current.

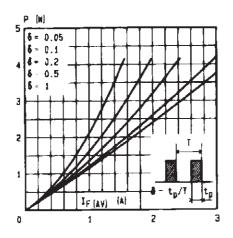


Fig.3: Thermal resistance versus lead length.

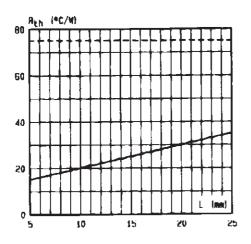
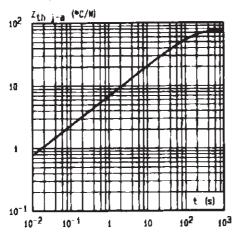
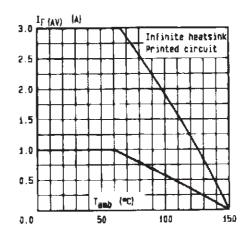


Fig. 4: Transient thermal impedance junction ambient for mounting $n^{\circ} 2$ versus pulse duration (L = 10 mm).



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Fig. 2: Average forward current versus ambient temperature.



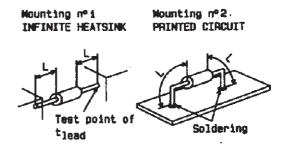


Fig. 5: Peak forward current versus peak forward voltage drop (maximum values).

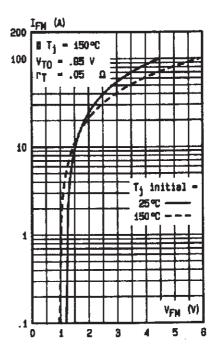


Fig. 7: Recovery time versus dl_F/dt.

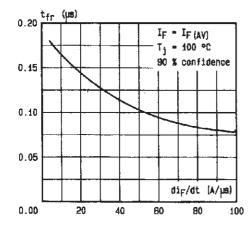


Fig. 9: Peak reverse current versus dl_F/dt.

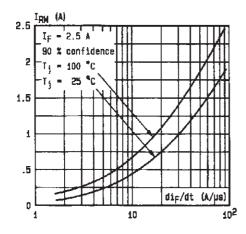


Fig. 11: Dynamic parameters versus junction temperature.

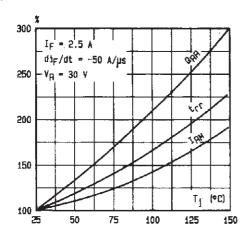


Fig. 8: Peak forward voltage versus dl_F/dt.

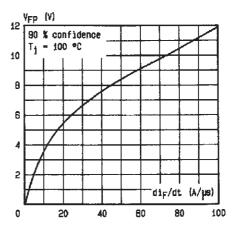


Fig. 10: Recovery charge versus dI_F/dt (typical values).

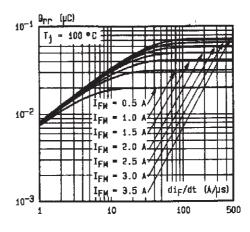
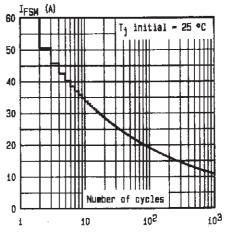
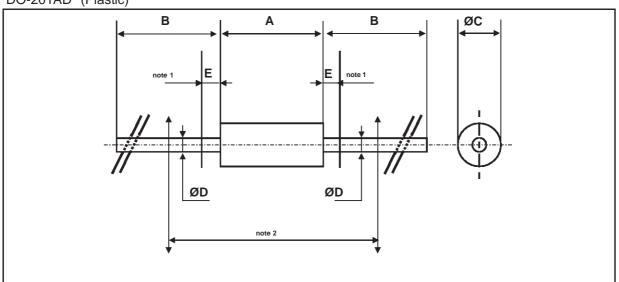


Fig. 12: Non repetitive surge peak current versus number of cycle.



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PACKAGE MECHANICAL DATA DO-201AD (Plastic)



| | | DIMENSIONS | | | |
|------|--------|------------|--------|-------|---|
| REF. | Millim | neters | Inches | | NOTES |
| | Min. | Max. | Min. | Max. | |
| A | | 9.50 | | 0.374 | 1 - The lead diameter \varnothing D is not controlled over zone E |
| В | 25.40 | | 1.000 | | 2 - The minimum axial length within which the device may be |
| ØC | | 5.30 | | 0.209 | placed with its leads bent at right angles is 0.59"(15 mm) |
| ØD | | 1.30 | | 0.051 | |
| E | | 1.25 | | 0.049 | |

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